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**FACSIMILE TRANSMISSION COVER SHEET**

**Date:** September 22, 2004

**To:** United States Patent and Trademark Office  
Examiner: Thien F. Tran; Art Unit: 2811

**Fax:** (703) 872-9306

**Re:** **Application Serial No.: 10/678,445**  
Filing Date: 10/3/2003; First Named Inventor: George Jonathan Kluth  
Attorney Docket No.: 0180146

**From:** Farjami & Farjami LLP

**Number of pages including the cover sheet:** 7

**Message:**

Enclosed please find the Amendment and Response to the Office Action dated September 10, 2004.

Thank you.

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Attorney Docket No.: 0180146

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Application of: Kluth, et al.

Art Unit: 2811

Serial No.: 10/678,445

Examiner: Tran, Thien F.

Filed: October 3, 2003

For: **Method for Forming Polysilicon Gate  
On High-K Dielectric and Related  
Structure**

**AMENDMENT AND RESPONSE TO OFFICE ACTION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the Office Action dated September 10, 2004 in the above-referenced patent application. Please enter and consider the following amendments and remarks.